TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (L<sup>2</sup>-π-MOSV)

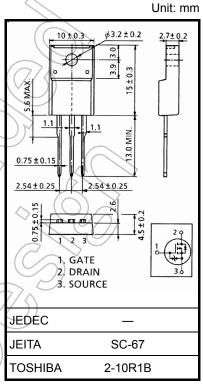
## 2SJ380

# Relay Drive, DC-DC Converter and Motor Drive Applications

- 4-V gate drive
- Low drain-source ON resistance: RDS (ON) =  $0.15 \Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 7.7 \text{ S (typ.)}$
- Low leakage current:  $IDSS = -100 \mu A (max) (VDS = -100 V)$
- Enhancement mode:  $V_{th} = -0.8 \text{ to } -2.0 \text{ V (V}_{DS} = -10 \text{ V}, I_D = -1 \text{ mA})$

### **Absolute Maximum Ratings (Ta = 25°C)**

| Characteris                        | stics                | Symbol           | Rating     | Unit       |  |
|------------------------------------|----------------------|------------------|------------|------------|--|
| Drain-source voltage               |                      | $V_{DSS}$        | -100       | V          |  |
| Drain-gate voltage (R <sub>G</sub> | S = 20 kΩ)           | $V_{DGR}$        | -100       | \<br>\     |  |
| Gate-source voltage                |                      | $V_{GSS}$        | ±20        | ∨ v        |  |
| Drain current                      | DC (Note 1)          | I <sub>D</sub>   | -12        | Α          |  |
|                                    | Pulse (Note 1)       | I <sub>DP</sub>  | -48        |            |  |
| Drain power dissipation            | n (Tc = 25°C)        | P <sub>D</sub>   | 35         | / (w       |  |
| Single pulse avalanche             | e energy<br>(Note 2) | EAS              | 312        | mJ         |  |
| Avalanche current                  |                      | JAR              | -12        | A          |  |
| Repetitive avalanche e             | nergy (Note 3)       | EAR              | 3.5        | μJ         |  |
| Channel temperature                | . (1                 | Tch              | 150        | ~c>        |  |
| Storage temperature ra             | ange                 | T <sub>stg</sub> | -55 to 150 | <b>℃</b> C |  |



Weight: 1.9 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

| Characteristics                        | Symbol                 | Max  | Unit |
|--|------------------------|------|------|
| Thermal resistance, channel to case    | R <sub>th (ch-c)</sub> | 3.57 | °C/W |
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 62.5 | °C/W |

Note1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = -25~V$ ,  $T_{ch} = 25^{\circ}C$  (initial), L = 2.94~mH,  $R_G = 25~\Omega$ ,  $I_{AR} = -12~A$ 

Note 3: Repetitive rating: pulse width limited by maximum junction temperature

This transistor is an electrostatic-sensitive device. Handle with care.

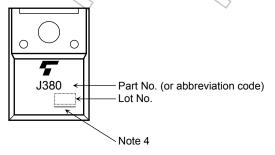
#### **Electrical Characteristics (Ta = 25°C)**

| Chara  | acteristics    | Symbol               | Test Condition   | Min  | Тур.         | Max          | Unit |
|--|----------------|----------------------|--|------|--------------|--------------|------|
| Gate leakage cur                                   | rent           | I <sub>GSS</sub>     | $V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$  | _    | _            | ±10          | μΑ   |
| Drain cut-off curre                                | ent            | I <sub>DSS</sub>     | $V_{DS} = -100 \text{ V}, V_{GS} = 0 \text{ V}$  | _    | _            | -100         | μА   |
| Drain-source brea                                  | akdown voltage | V (BR) DSS           | $I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$   | -100 | _            | _            | V    |
| Gate threshold vo                                  | oltage         | V <sub>th</sub>      | $V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$  | 0.8  | _            | -2.0         | V    |
| Drain-source ON                                    | resistance     | R <sub>DS (ON)</sub> | $V_{GS} = -4 \text{ V}, I_D = -6 \text{ A}$ $V_{GS} = -10 \text{ V}, I_D = -6 \text{ A}$ |      | 0.25<br>0.15 | 0.32<br>0.21 | Ω    |
| Forward transfer                                   | admittance     | Y <sub>fs</sub>      | V <sub>DS</sub> = -10 V, I <sub>D</sub> = -6 A   | 4.5  | 7.7          | _            | S    |
| Input capacitance                                  |                | C <sub>iss</sub>     |  | _    | 1100         | _            | pF   |
| Reverse transfer capacitance                       |                | C <sub>rss</sub>     | $V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$                        | _    | 200          |              | pF   |
| Output capacitance                                 |                | C <sub>oss</sub>     |  | _    | 440          | _            | pF   |
| Switching time                                     | Rise time      | t <sub>r</sub>       | 0 V ¬  | - {  | 18           | V /          |      |
|  | Turn-on time   | t <sub>on</sub>      | V <sub>GS</sub> V <sub>OUT</sub> C <sub>R</sub> R <sub>N</sub>                           |      | 30           | ) —          |      |
|  | Fall time      | t <sub>f</sub>       | C  | (A)  | 18           | _            | ns   |
|  | Turn-off time  | t <sub>off</sub>     | Duty ≤ 1%, t <sub>W</sub> = 10 μs  | ) –  | 65           | _            |      |
| Total gate charge<br>(gate-source plus gate-drain) |                | Qg                   | $V_{DD} \approx -80 \text{ V}, V_{GS} = -10 \text{ V},$                                  |      | 48           |              | nC   |
| Gate-source charge                                 |                | Q <sub>gs</sub>      | lp = −12 A   |      | 29           | _            | nC   |
| Gate-drain ("miller") charge                       |                | Qgd                  |  |      | 19           | _            | nC   |

## Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol           | Test Condition                                 | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Continuous drain reverse current (Note 1) | IDR              | -  | _   | _    | -12 | Α    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub> | _  |     |      | -48 | Α    |
| Forward voltage (diode)                   | VDSF             | $I_{DR} = -12 \text{ A}, V_{GS} = 0 \text{ V}$ | _   | _    | 1.7 | V    |
| Reverse recovery time                     | tir              | $I_{DR} = -12 \text{ A}, V_{GS} = 0 \text{ V}$ | _   | 160  | _   | ns   |
| Reverse recovery charge                   | Qu               | dI <sub>DR</sub> /dt = 50 A/μs                 | _   | 0.5  | _   | μС   |

### Marking

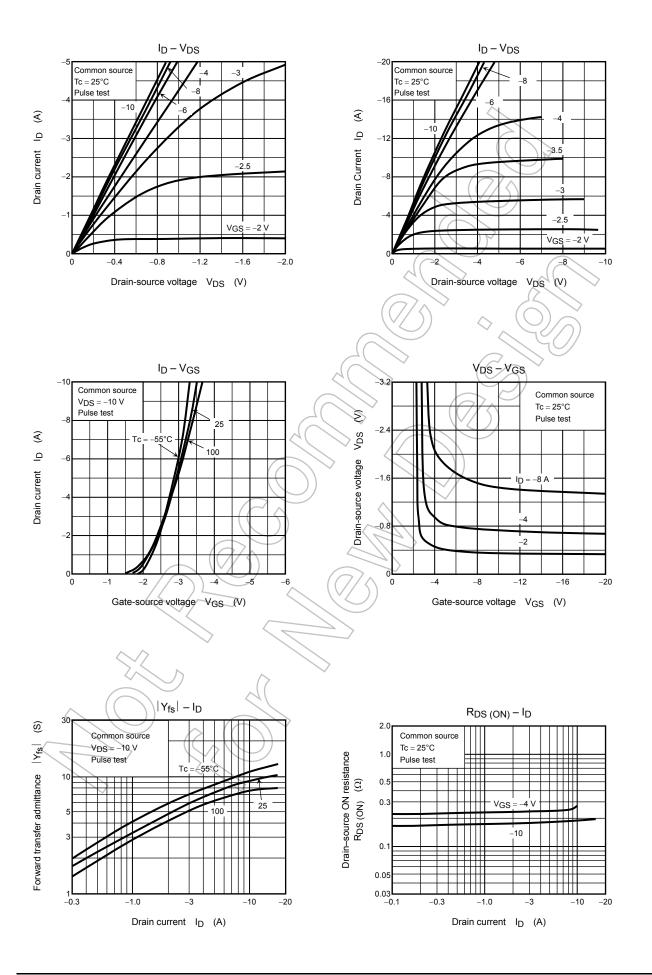


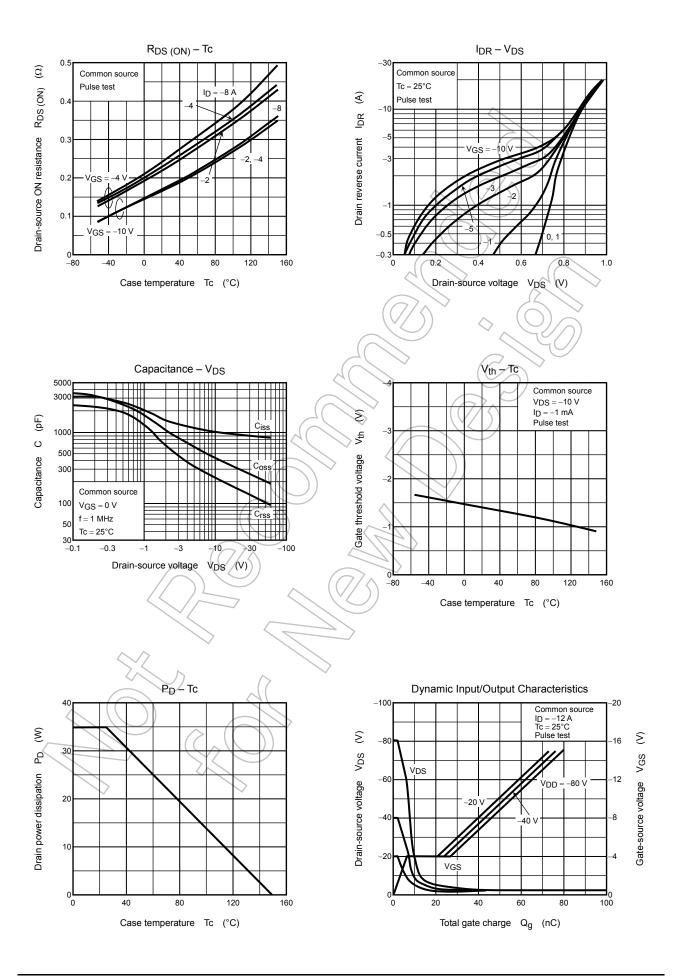
Note 4: A line under a Lot No. identifies the indication of product Labels.

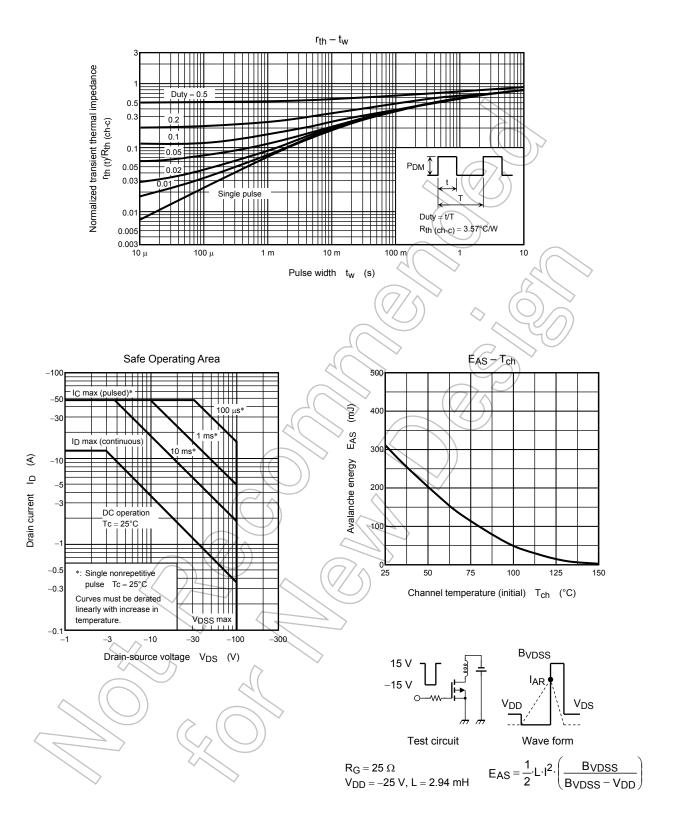
Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

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6